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## **RFMD(R) Extends Portfolio of GaN Wideband Power Amplifiers**

Company Begins Shipping New GaN Product To Top-Tier Military Supplier

HONOLULU--(BUSINESS WIRE)--June 5, 2007--RF Micro Devices, Inc. (NASDAQ: RFMD), a global leader in the design and manufacture of high-performance radio systems and solutions for applications that drive mobile communications, today announced it has commenced shipments of its gallium nitride (GaN) RF3822 PowerIC broadband power amplifier (PA) to a top-tier military supplier. RFMD's RF3822 PowerIC delivers power performance over a frequency range of 0.1GHz to 1GHz and is ideally suited for multiple-band and broadband applications, such as software-defined radios (SDRs) for military communications.

RFMD anticipates the inherent performance advantages of its GaN technology, relative to competing technologies, give it the potential to penetrate high power amplifier (HPA) applications, such as military and wireless infrastructure, in much the same way GaAs HBT became the dominant technology for cellular power amplifiers.

According to Asif Anwar, Director of the Strategy Analytics GaAs and Compound Semiconductor market research service, "Gallium nitride transistors and ICs from RFMD and a few other suppliers will capture a significant share of the \$720+ million per year market for power amplifiers for 3G and WiMAX infrastructure, as well as a share in military and defense applications that require semiconductors with high RF output power and high efficiency with high bandwidth."

Jeff Shealy, vice president of RFMD's infrastructure product group, said, "These first shipments of RFMD's RF3822 demonstrate the increasing customer interest we are receiving in our GaN technology and associated GaN product portfolio. RFMD continues to attract very favorable customer interest from new and existing customers in multiple growth markets, including military communications, wireless infrastructure, public mobile radio, general purpose amplifiers and high power radar."

Bob Bruggeworth, RFMD's president and CEO, added, "RFMD's newly introduced GaN products are a natural fit with the existing multi-market products we manufacture using our proprietary GaAs technology. As the world's largest manufacturer of GaAs, RFMD brings tremendous leverage to these markets by utilizing the same manufacturing assets we employ to service the high-volume cellular handset market. RFMD is leveraging our core strengths and leadership position in the cellular market to drive opportunities for revenue and customer diversification in new, high-growth markets."

RFMD's 28V GaN 10W RF3822 PowerIC is optimized for high efficiency with 16dB gain over a very wide operating bandwidth in a 50 ohm impedance environment. The RF3822 utilizes advanced heat sink and power dissipation technologies to deliver high output power with constant gain and excellent thermal stability.

The RF3822 is part of RFMD's RF382X product family and is packaged in a low-cost, surface-mountable aluminum nitride package that is footprint compatible with industry-standard SOIC-8 packages. RFMD's RF382X product family offers integrated passive technology to achieve impedance matching and delivers very high peak efficiency across a wide range of frequencies. The RF382X product family is ideal for applications such as 3G cellular infrastructure, military communications, software definable radios (SDRs) and public mobile radio.

In January, RFMD received a purchase order for its RF3825 GaN PowerIC broadband power amplifier from the same top-tier military supplier. The RF3825 is a 10-watt device capable of servicing a frequency band from 0.2GHz to 1.9GHz. RFMD is providing a demonstration of its RF3825 28V broadband PowerIC at a frequency range of 225MHz to 1800MHz during the IEEE MTT-S International Microwave Symposium 2007 in Honolulu, Hawaii on June 5-7 at Booth 801.

About RFMD: RF Micro Devices, Inc. (NASDAQ: RFMD) is a global leader in the design and manufacture of high-performance radio systems and solutions for applications that drive mobile communications. RFMD's power amplifiers, transmit modules, cellular transceivers and system-on-chip (SoC) solutions enable worldwide mobility, provide enhanced connectivity and support advanced functionality in current- and next-generation mobile handsets, cellular base stations, wireless local area networks (WLANs) and global positioning systems (GPS). Recognized for its diverse portfolio of state-of-the-art semiconductor technologies and vast RF systems expertise, RFMD is a preferred supplier enabling the world's leading mobile device manufacturers to deliver advanced wireless capabilities that satisfy current and future market demands.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering,

design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at [www.rfmd.com](http://www.rfmd.com).

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in quarterly operating results, the rate of growth and development of wireless markets, risks associated with the operation of our wafer fabrication facilities, molecular beam epitaxy facility, assembly facility and test and tape and reel facilities, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, our ability to reduce costs and improve gross margins by implementing innovative technologies, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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